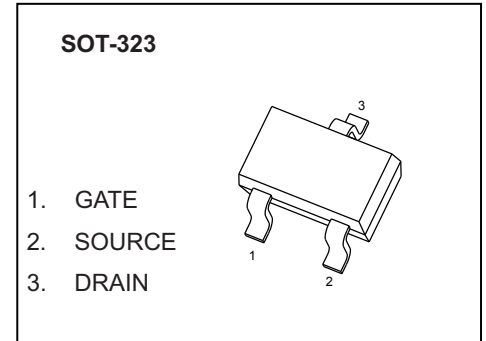


SOT-323 Plastic-Encapsulate MOSFETS

2N7002KW N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60 V	5Ω@10V	340mA
	5.3Ω@4.5V	



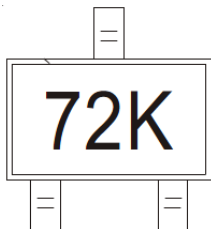
FEATURE

- High density cell design for Low $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability
- ESD protected

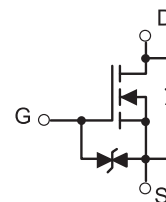
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



MOSFET MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	340	mA
I_{DM}	Pulsed Drain Current(note1)	800	mA
P_D	Power Dissipation	0.2	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	°C/W

MOSFET ELECTRICAL CHARACTERISTICS

$T_a = 25^\circ\text{C}$ unless otherwise specified

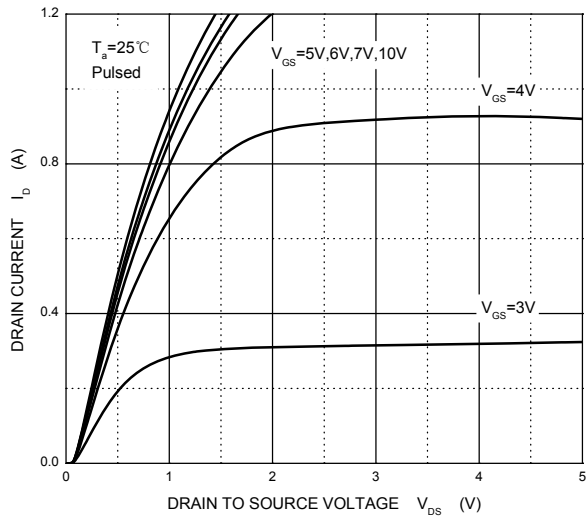
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source Breakdown Voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D =250μA	60			V
GateThreshold Voltage (note 2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =1mA	1	1.3	2.5	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} = 0V			1	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V			±10	μA
Drain-Source On-Resistance (note 2)	R _{DS(on)}	V _{GS} =4.5V, I _D =200mA		1.1	5.3	Ω
		V _{GS} =10V, I _D =500mA		0.9	5	Ω
DYNAMIC PARAMETERS (note 3)						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f =1MHz			40	pF
Output Capacitance	C _{oss}				30	pF
Reverse Transfer Capacitance	C _{rss}				10	pF
SWITCHING PARAMETERS(note 3)						
Turn-on Delay Time	t _{d(on)}	V _{GS} =10V, V _{DD} =50V, R _G =50Ω			10	ns
Turn-off Delay Time	t _{d(off)}		R _{GS} =50Ω, R _L =250Ω			15
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =300mA, V _R =25V, dI _S /dt=-100A/us		30		ns
Recovered Charge	Q _r	V _{GS} =0V, I _S =300mA, V _R =25V dI _S /dt=-100A/us		30		nC
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV _{GSO}	I _{gs} =± 1mA(Open Drain)	± 21.5		± 30	V
DRAIN-SOURCE DIODE						
Diode Forward Voltage(note 2)	V _{SD}	I _S =300mA, V _{GS} = 0V			1.5	V
Continuous Diode Forward Current	I _S				0.2	A
Pulsed Diode Forward Current(note1)	I _{SM}				0.53	A

Notes :

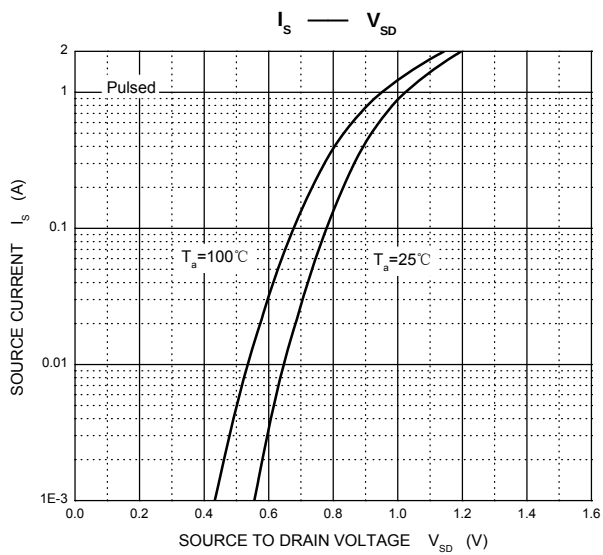
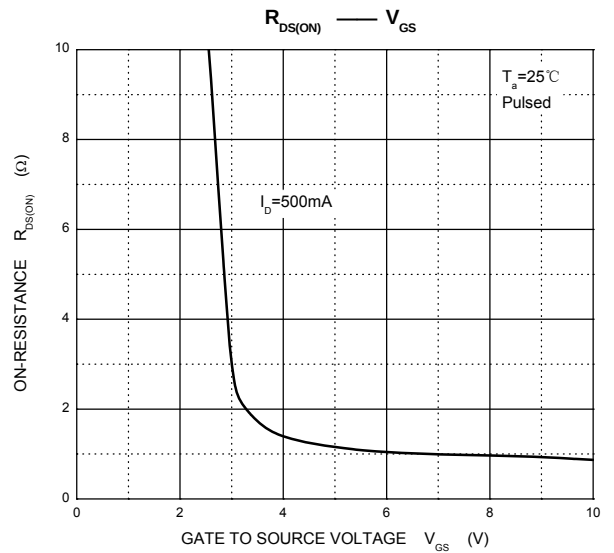
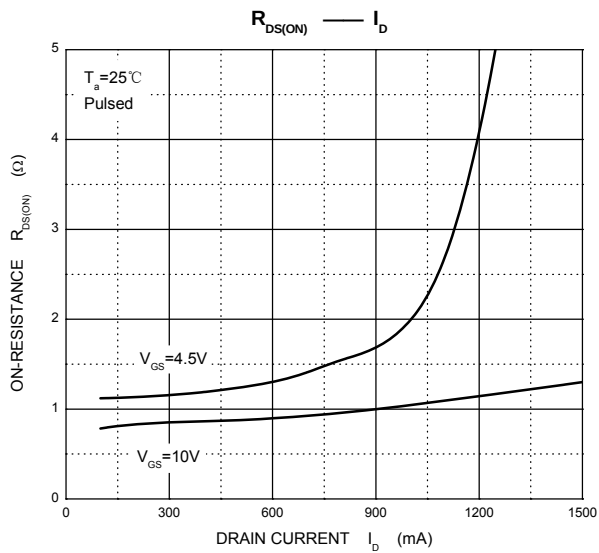
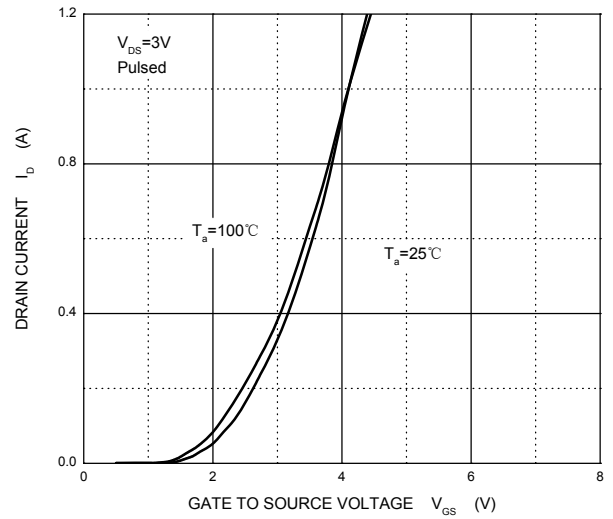
1. Repetitive rating: Pluse width limited by junction temperature.
2. Pulse Test : Pulse width $\leq 300\mu s$, duty cycles $\leq 2\%$.
3. Guaranteed by design, not subject to production testing.

Typical Characteristics

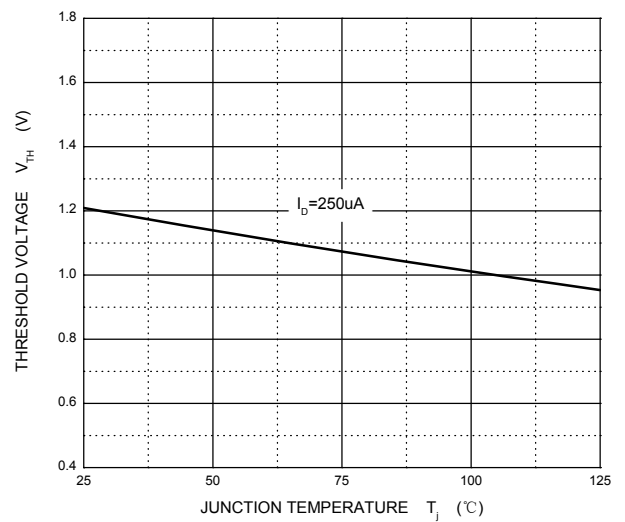
Output Characteristics



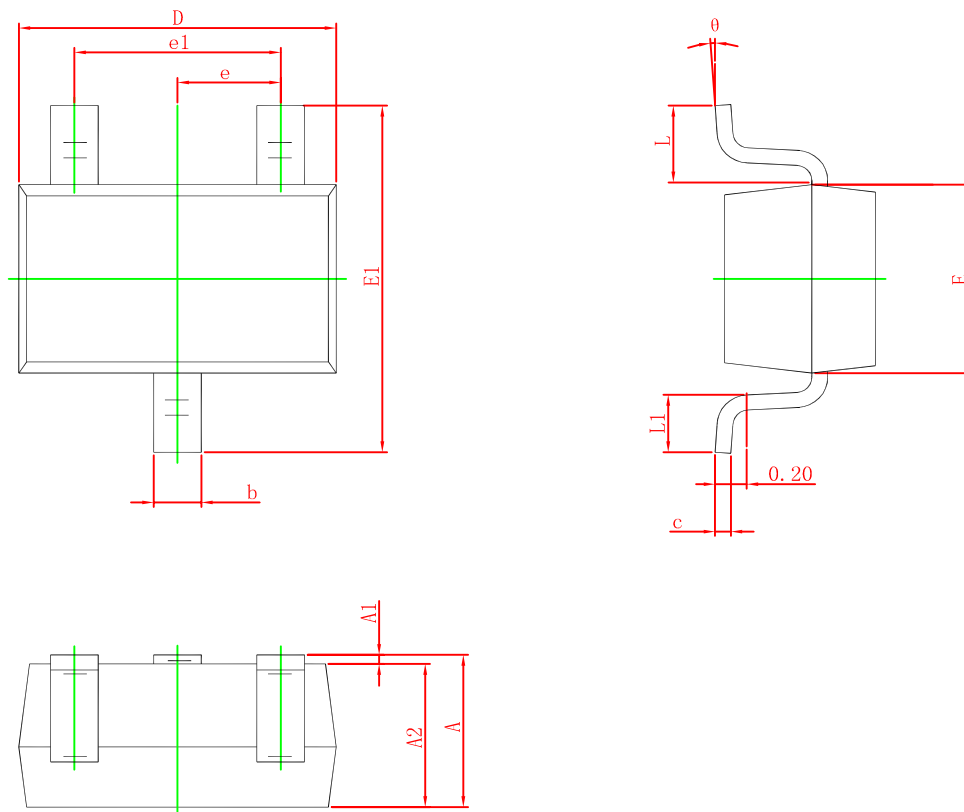
Transfer Characteristics



Threshold Voltage



SOT-323 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°